

C. Amendments to the Claims.

1. (Previously Presented) A memory cell, comprising:

a first node for storing a first potential;  
a second node for storing a second potential;  
transistor gates formed from a gate layer; and  
a capacitor having plates coupled between the first node and  
second node, a portion of at least one plate of the capacitor comprising a  
first interconnect wiring formed over the gate layer and includes a plurality  
of conductive layers that interconnects circuit components of the memory  
cell.

2. (Original) The memory cell of claim 1, further comprising:

a first inverter having an input coupled to the first node and an  
output coupled to the second node; and  
a second inverter having an input coupled to the second node  
and an output coupled to the first node; wherein  
the first node stores a true data value and the second node  
stores a complementary data value.

3. (Original) The memory cell of claim 1, further including:

a first access transistor coupled to the first node; and  
a second access transistor coupled to the second node.

4. (Cancelled)

5. (Previously Presented) The memory cell of claim 1, wherein:

the first conductive interconnect wiring includes a bottom  
conductive layer, a dielectric layer formed over the bottom conductive  
layer, and a top conductive layer formed over the dielectric layer, the top  
conductive layer forming at least a portion of the first plate of the  
capacitor.

6. (Previously Presented) The memory cell of claim 1, further including:

a second conductive interconnect wiring formed over the first  
conductive interconnect wiring that forms at least a portion of a second  
plate of the capacitor.

5 7. (Original) The memory cell of claim 6, wherein:

the second conductive interconnect wiring comprises titanium;  
the bottom conductive layer comprises titanium nitride; and  
the top conductive layer comprises titanium.

10 8. (Cancelled)

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25 16. (Cancelled)

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18. (Cancelled)

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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**19. (Cancelled)**

**20. (Cancelled)**

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